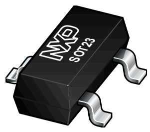


PMV65XP

20 V, single P-channel Trench MOSFET

12 February 2013 — Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Low on-state resistance
- Trench MOSFET technology

3. Applications

- Low power DC-to-DC converters
- Load switching
- Battery management
- Battery powered portable equipment

4. Quick reference data

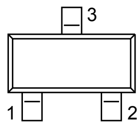
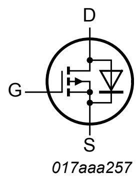
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	T_j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-12	-	12	V
I_D	drain current	V_{GS} = -4.5 V; T_{sp} = 25 °C		-	-	-4.3	A
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -2.8 A; T_j = 25 °C		-	58	74	mΩ

Scan or click this QR code to view the latest information for this product

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 TO-236AB (SOT23)	
2	S	source		
3	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMV65XP	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV65XP	%M9

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T_j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-12	12	V
I_D	drain current	V_{GS} = -4.5 V; T_{sp} = 25 °C		-	-4.3	A
		V_{GS} = -4.5 V; T_{amb} = 25 °C	[1]	-	-2.8	A
		V_{GS} = -4.5 V; T_{amb} = 100 °C	[1]	-	-1.8	A
I_{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \leq 10$ µs		-	-16	A
P_{tot}	total power dissipation	T_{amb} = 25 °C	[2]	-	480	mW
			[1]	-	833	mW
		T_{sp} = 25 °C		-	4165	mW

Symbol	Parameter	Conditions		Min	Max	Unit
T_j	junction temperature			-55	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C
Source-drain diode						
I_S	source current	T_{sp} = 25 °C		-	-1.6	A

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm^2.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

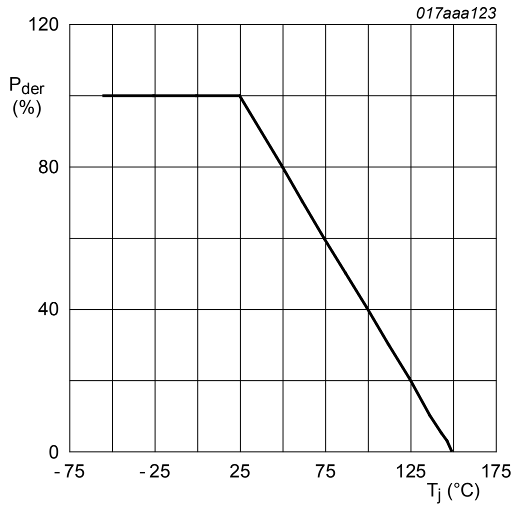


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\ \%$$

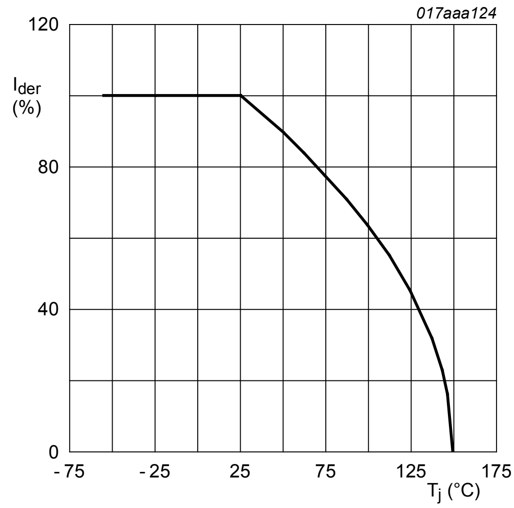
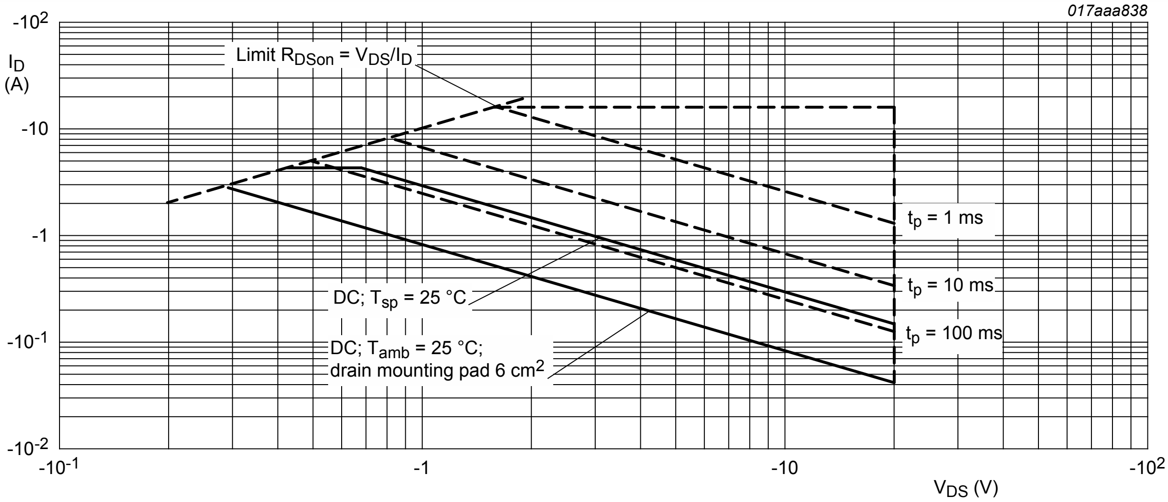


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25°C)}} \times 100\ \%$$



I_{DM} = single pulse

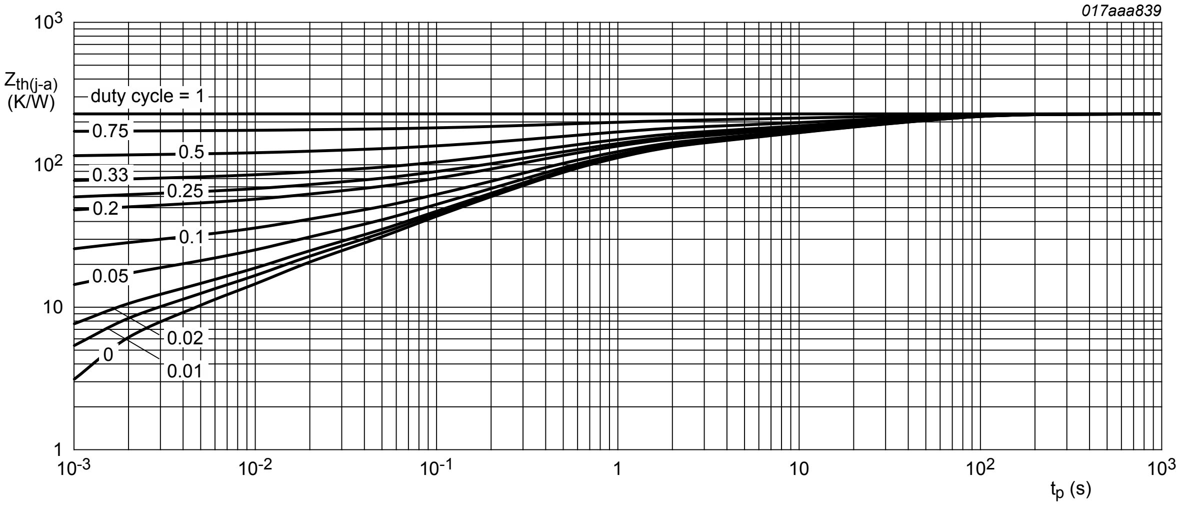
Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

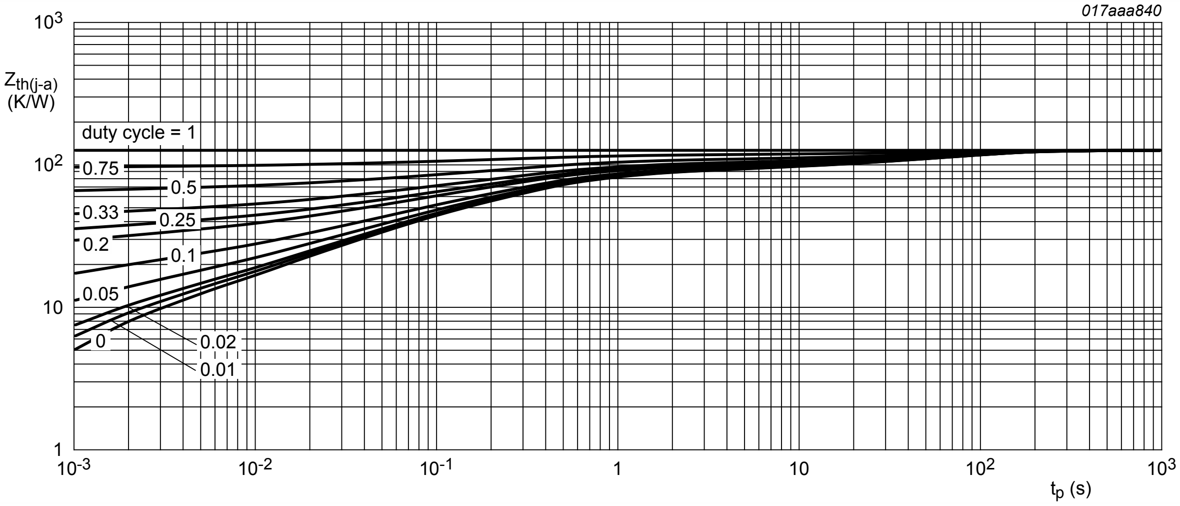
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	230	260	K/W
			[2]	-	125	150	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	25	30	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm^2.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm^2

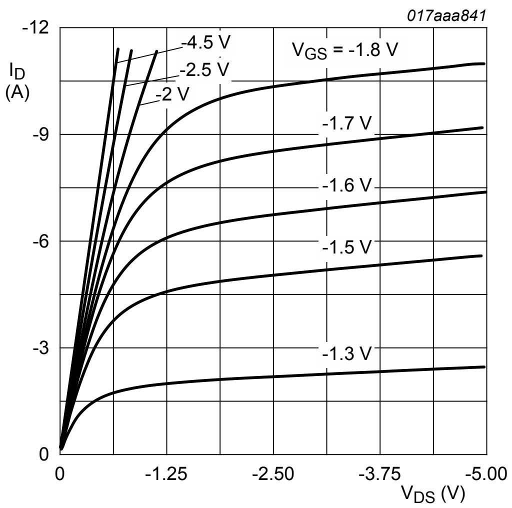
Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

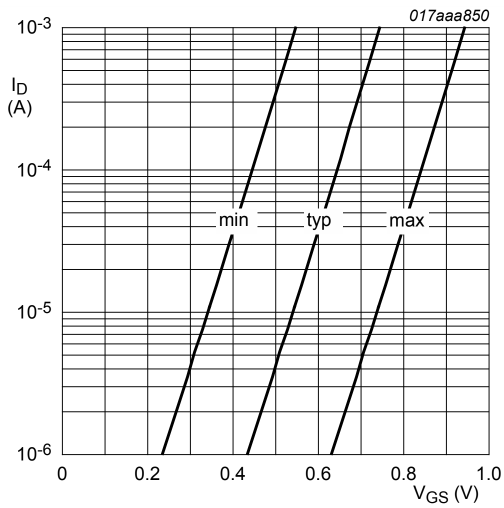
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = -250 µA; V_{GS} = 0 V; T_j = 25 °C		-20	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = -250 µA; V_{DS} = V_{GS}; T_j = 25 °C		-0.47	-0.65	-0.9	V
I_{DSS}	drain leakage current	V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C		-	-	-1	µA
		V_{DS} = -20 V; V_{GS} = 0 V; T_j = 150 °C		-	-	-100	µA

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I_{GSS}	gate leakage current	V_{GS} = -12 V; V_{DS} = 0 V; T_j = 25 °C		-	-	-100	nA
		V_{GS} = 12 V; V_{DS} = 0 V; T_j = 25 °C		-	-	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -2.8 A; T_j = 25 °C		-	58	74	mΩ
		V_{GS} = -4.5 V; I_D = -2.8 A; T_j = 150 °C		-	82	105	mΩ
		V_{GS} = -2.5 V; I_D = -2.3 A; T_j = 25 °C		-	67	92	mΩ
		V_{GS} = -1.8 V; I_D = -1 A; T_j = 25 °C		-	87	135	mΩ
g_{fs}	forward transconductance	V_{DS} = -10 V; I_D = -2.8 A; T_j = 25 °C		-	15	-	S
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	V_{DS} = -6 V; I_D = -2.8 A; V_{GS} = -4.5 V; T_j = 25 °C		-	7.7	-	nC
Q_{GS}	gate-source charge			-	1	-	nC
Q_{GD}	gate-drain charge			-	1.65	-	nC
C_{iss}	input capacitance	V_{DS} = -20 V; f = 1 MHz; V_{GS} = 0 V; T_j = 25 °C		-	744	-	pF
C_{oss}	output capacitance			-	65	-	pF
C_{rss}	reverse transfer capacitance			-	53	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = -6 V; V_{GS} = -4.5 V; $R_{G(ext)}$ = 6 Ω; T_j = 25 °C; I_D = -1 A		-	7	-	ns
t_r	rise time			-	18	-	ns
$t_{d(off)}$	turn-off delay time			-	135	-	ns
t_f	fall time			-	68	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	I_S = -0.9 A; V_{GS} = 0 V; T_j = 25 °C		-	-0.8	-1.2	V



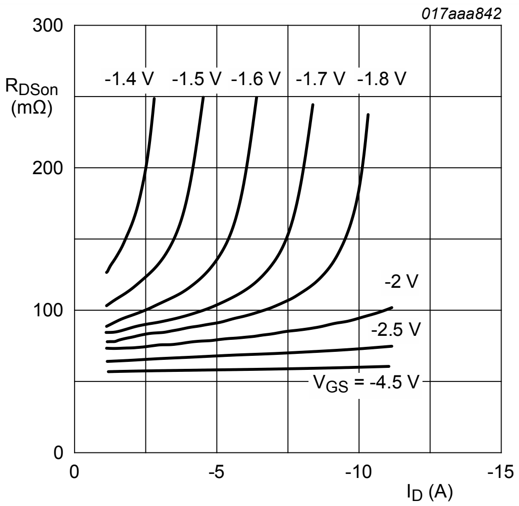
T_j = 25 °C

Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



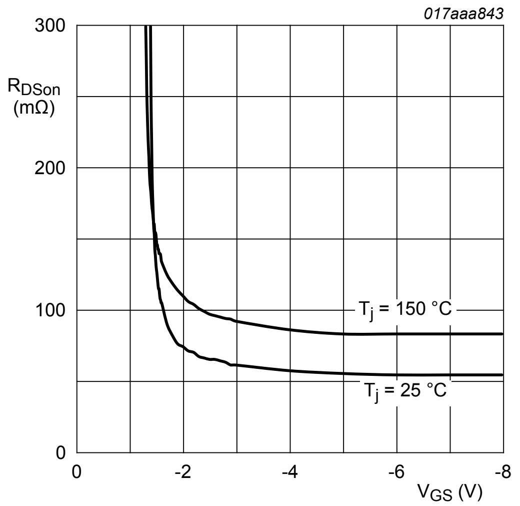
T_j = 25 °C; V_{DS} = -5 V

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



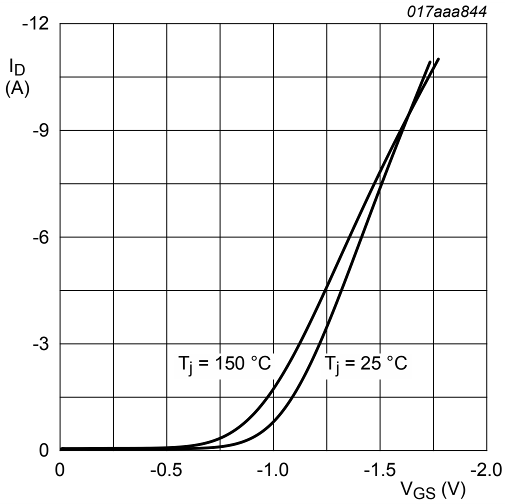
T_j = 25 °C

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



I_D = -2.8 A

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



$V_{DS} > I_D \times R_{DSon}$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

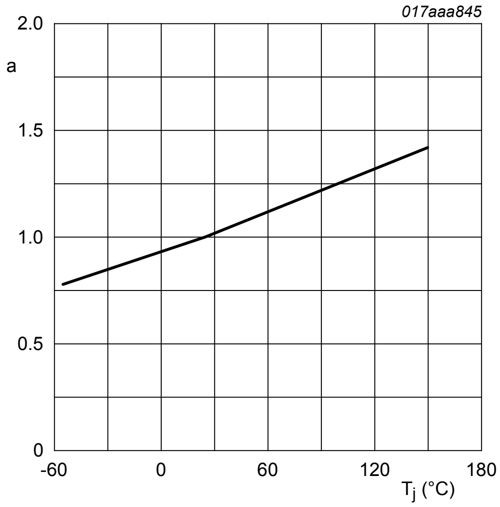
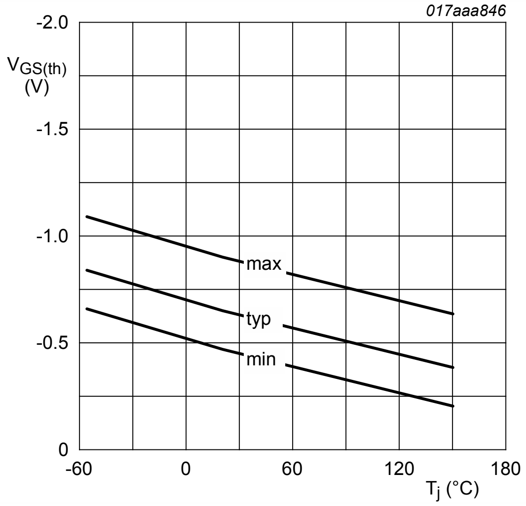


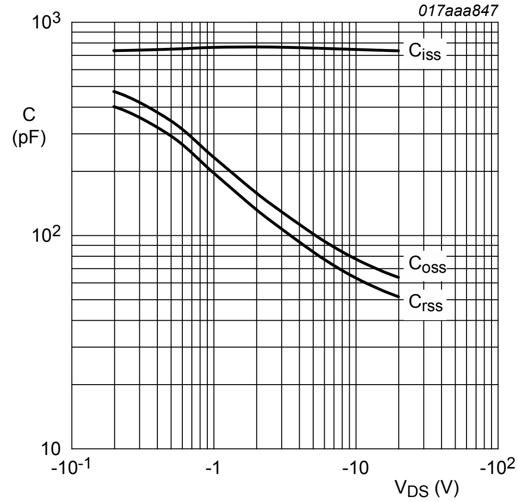
Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$



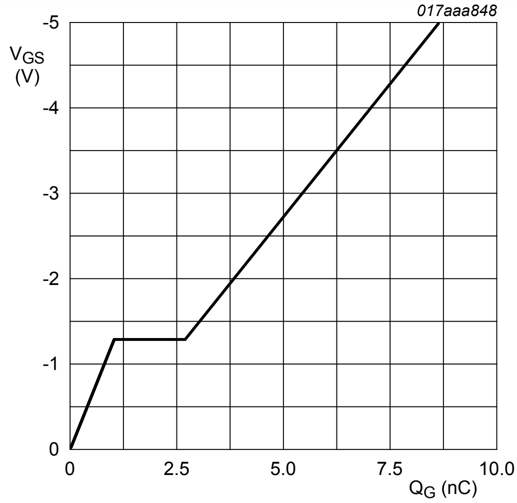
I_D = -0.25 mA; V_{DS} = V_{GS}

Fig. 12. Gate-source threshold voltage as a function of junction temperature



f = 1 MHz; V_{GS} = 0 V

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



I_D = -2.8 A; V_{DS} = -6 V; T_{amb} = 25 °C

Fig. 14. Gate-source voltage as a function of gate charge; typical values

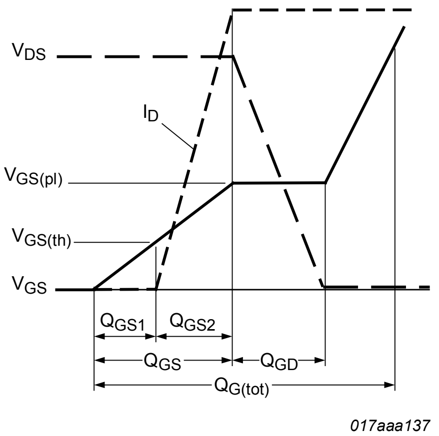
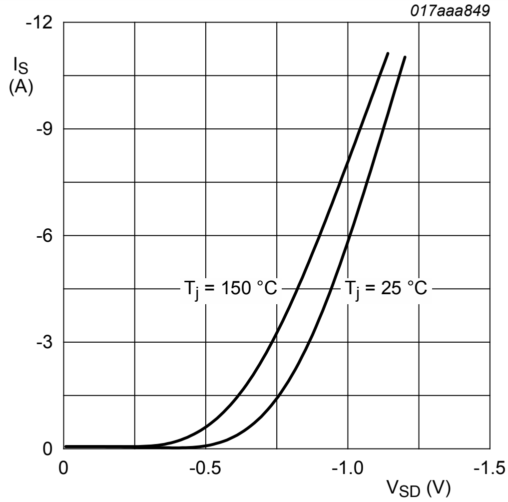


Fig. 15. Gate charge waveform definitions



V_{GS} = 0 V

(1) T_j = 150 °C

(2) T_j = 25 °C

Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

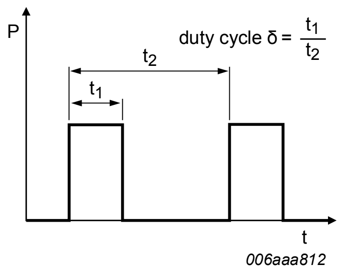


Fig. 17. Duty cycle definition

12. Package outline

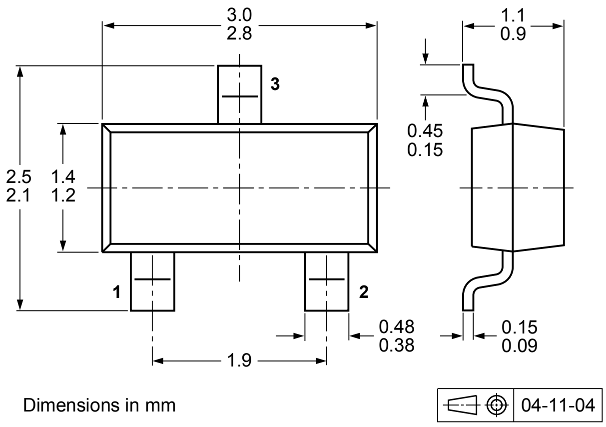


Fig. 18. Package outline TO-236AB (SOT23)

13. Soldering

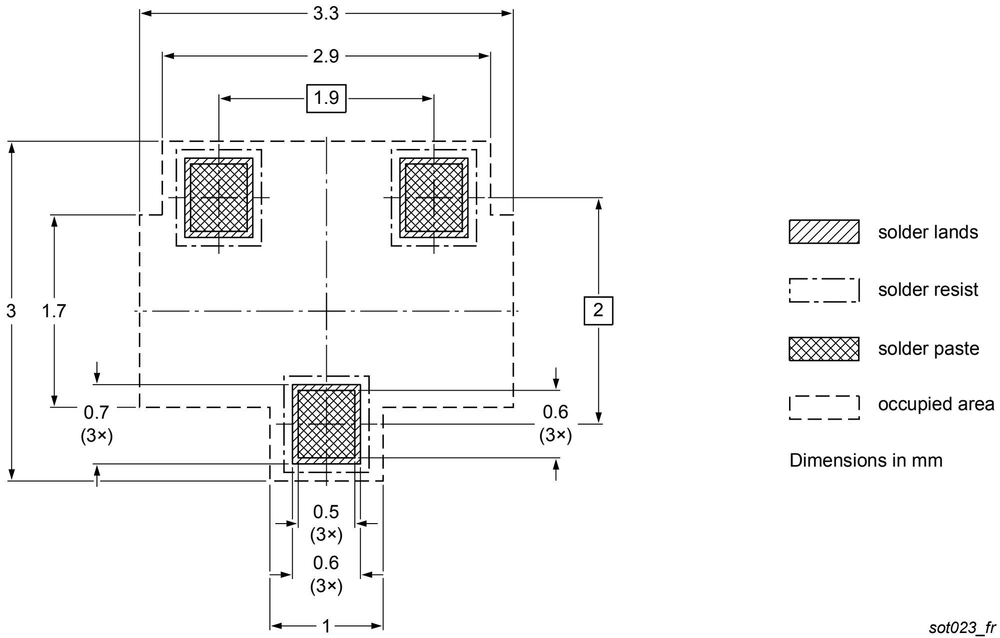


Fig. 19. Reflow soldering footprint for TO-236AB (SOT23)

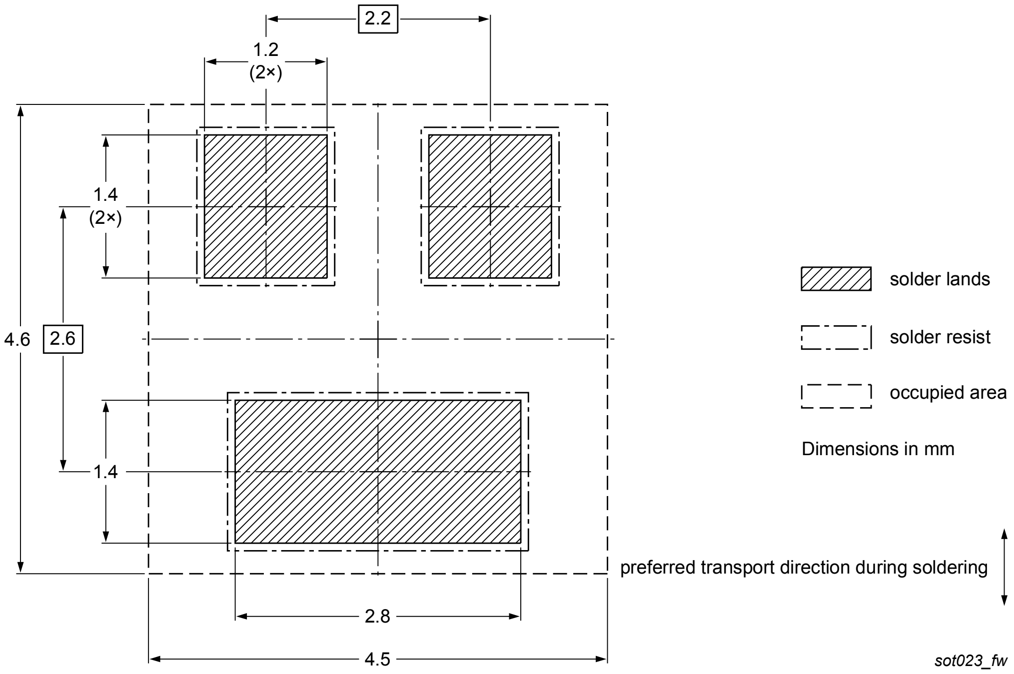


Fig. 20. Wave soldering footprint for TO-236AB (SOT23)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV65XP v.2	20130212	Product data sheet	-	PMV65XP v.1
Modifications:	• Pinning information corrected			
PMV65XP v.1	20120921	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
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